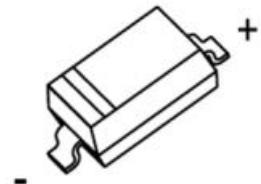


SOD-123 Schottky Barrier Rectifier Diode 肖特基势垒整流二极管**SOD-123****■Features 特点**

Low forward voltage drop 低正向压降
 High current capability 高电流能力
 Surface mount device 表面贴装器件
 Case 封装:SOD-123

**■Maximum Rating 最大额定值**

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	B5817W	B5818W	B5819W	Unit 单位
Device Marking 产品印字		SJ	SK	SL	
Peak Reverse Voltage 反向峰值电压	V _{RRM}	20	30	40	V
DC Reverse Voltage 直流反向电压	V _R	20	30	40	V
RMS Reverse Voltage 反向电压均方根值	V _{R(RMS)}	14	21	28	V
Forward Rectified Current 正向整流电流	I _F		1		A
Peak Surge Current 峰值浪涌电流	I _{FSM}		25		A
Repetitive Peak Surge Current 重复峰值浪涌电流	I _{FRM}		3		A
Power Dissipation 耗散功率	P _D		250		mW
Thermal Resistance J-A 结到环境热阻	R _{θJA}		400		°C/W
Junction Temperature 结温	T _J		-65 to +125		°C
Storage Temperature 储藏温度	T _{stg}		-65 to +150		°C

■Electrical Characteristics 电特性

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	B5817W	B5818W	B5819W	Unit 单位	Condition 条件
Reverse Voltage 反向电压	V _R	20	30	40	V	I _R =1mA
Forward Voltage 正向电压	V _F	0.45 0.75	0.5 0.875	0.55 0.9	V	I _F =1A I _F =3A
Reverse Current 反向电流	I _R	0.05 (Ta=25°C) 8 (Ta=100°C)			mA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _T	30			pF	V _R =4V, f=1MHz

■Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

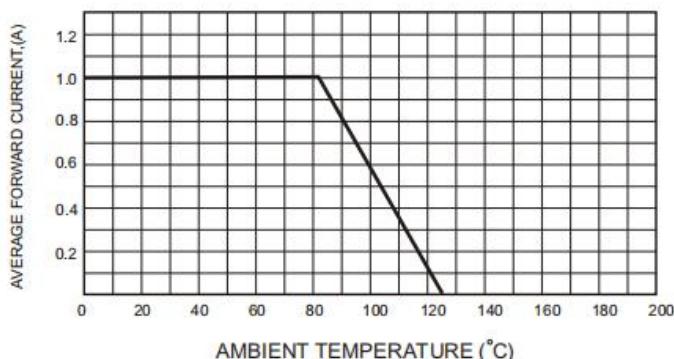


FIG.3 - Power Derating Curve

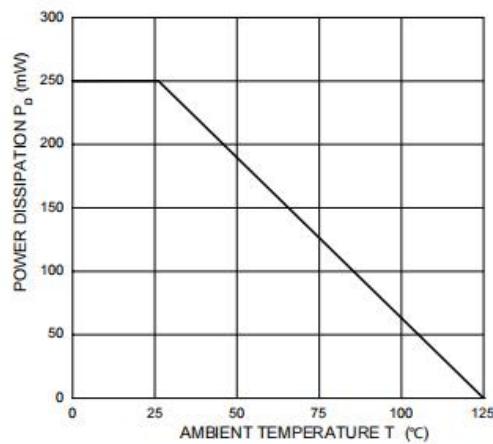


FIG.4-TYPICAL JUNCTION CAPACITANCE

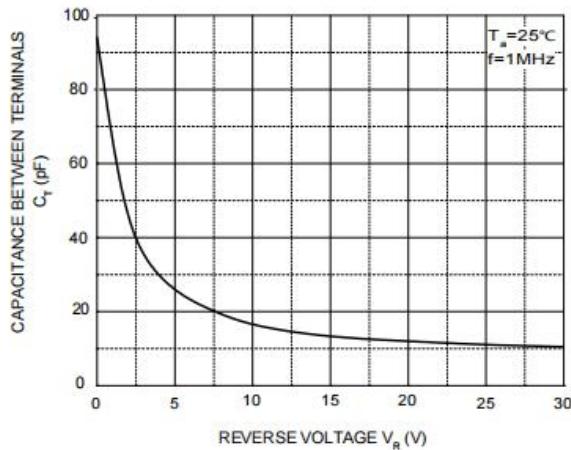


FIG.2-TYPICAL FORWARD

CHARACTERISTICS

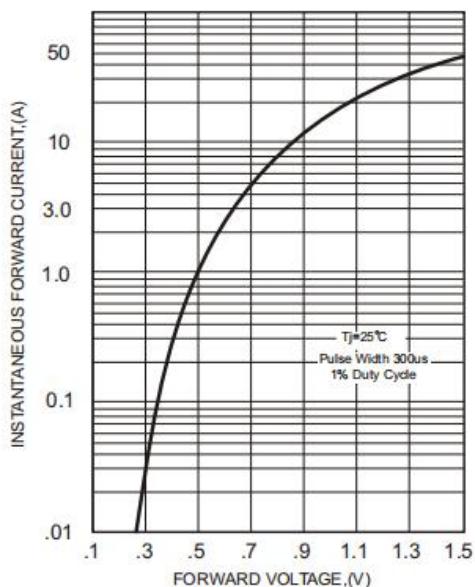
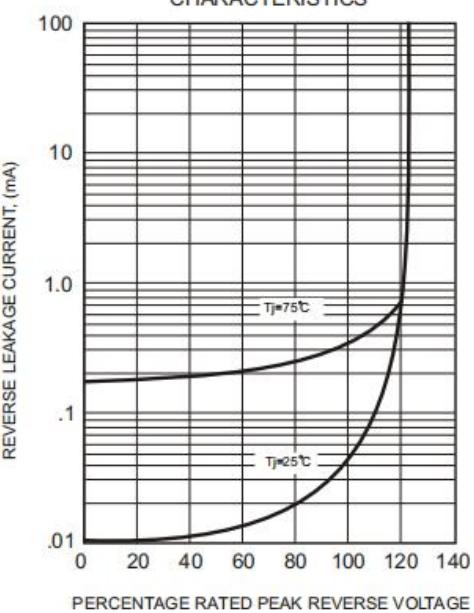
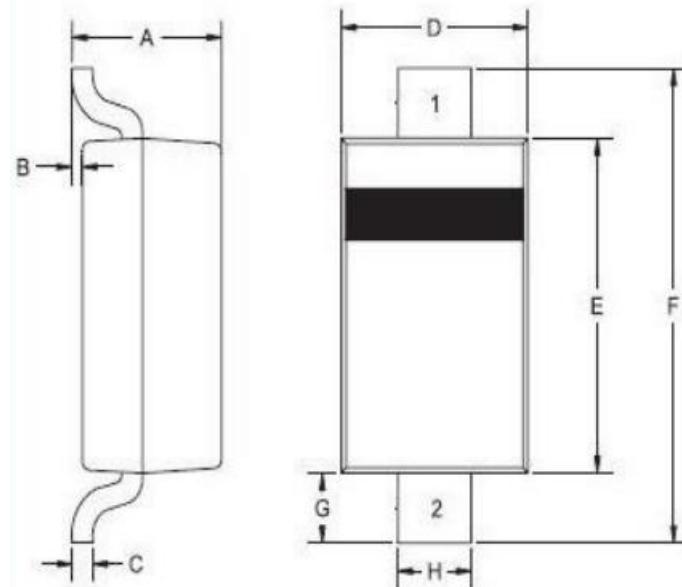


FIG.5 - TYPICAL REVERSE

CHARACTERISTICS



■ Dimension 外形封装尺寸 SOD-123



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.037	0.053	0.95	1.35
B	0.000	0.005	0.00	0.12
C	-	0.008	-	0.20
D	0.055	0.071	1.40	1.80
E	0.098	0.110	2.50	2.80
F	0.142	0.154	3.60	3.90
G	0.016	-	0.40	-
H	0.020	0.028	0.50	0.70